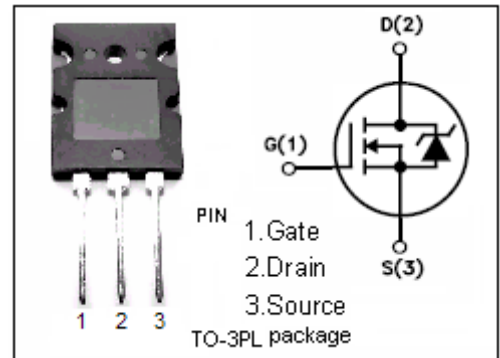


isc N-Channel MOSFET Transistor

2SK1020

DESCRIPTION

- Drain Current $-I_D=30A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=500V(\text{Min})$

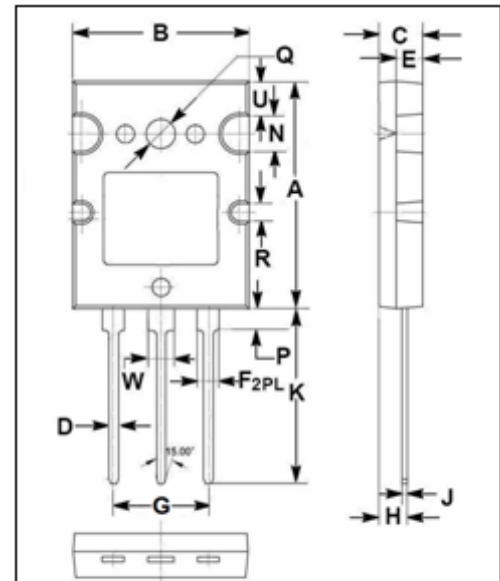


APPLICATIONS

- high voltage, high speed power switching

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	30	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	300	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	25.50	26.50
B	19.80	20.20
C	4.50	5.50
D	0.90	1.10
E	2.80	3.20
F	2.40	2.60
G	10.80	11.00
H	3.10	3.30
J	0.50	0.70
K	20.00	21.00
N	3.90	4.50
P	2.40	2.60
Q	3.10	3.50
R	1.90	2.60
U	3.90	4.10
W	2.90	3.25

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.416	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient		$^\circ C/W$

isc N-Channel Mosfet Transistor**2SK1020****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =1mA	2.5	3.5	5.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =15A		0.18	0.25	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =500V; V _{GS} = 0			500	uA
V _{SD}	Forward On-Voltage	I _S =30A; V _{GS} =0		1.1	1.70	V